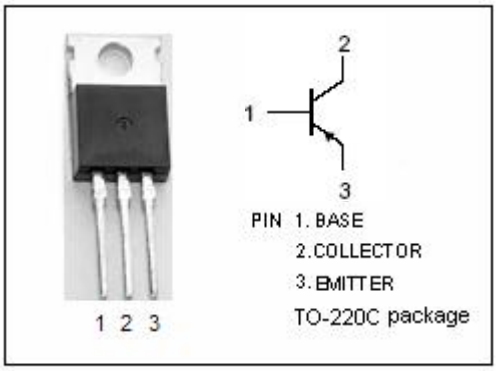
isc Silicon PNP Power Transistor — BDY82

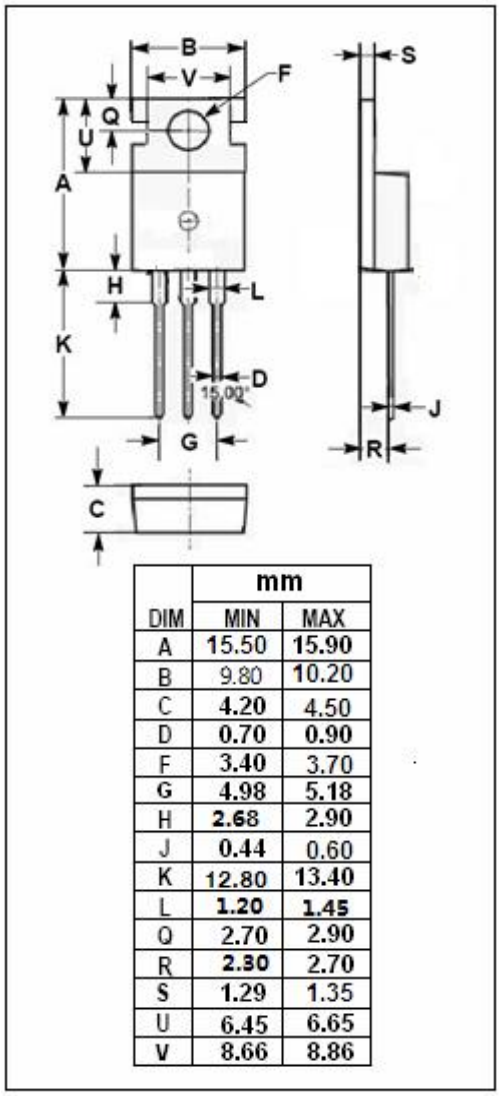


DESCRIPTION

- Continuous Collector Current-I_C= -4A
- Collector Power Dissipation-
  : P_C= 36W @T_C= 25℃
- Complement to Type BDY80
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for general purpose switching and amplifier applications.



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-35	V
V_{EBO}	Emitter-Base Voltage	-10	V
I_C	Collector Current-Continuous	-4	A
I_B	Base Current-Continuous	-2	A
P_C	Collector Power Dissipation@T_C=25℃	36	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	3.5	℃/W

isc Silicon PNP Power Transistor BDY82

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -30mA; I_B= 0	-35			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -1mA; I_E= 0	-35			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-10			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -0.05A			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -0.5A; V_{CE}= -5V			-0.9	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -20V; I_B= 0			-10	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= -20V; I_E= 0			-0.2	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-0.1	mA
h_{FE-1}	DC Current Gain	I_C= -0.5A; V_{CE}= -5V	40		240	
h_{FE-2}	DC Current Gain	I_C= -1A; V_{CE}= -5V	20			
f_T	Current Gain-Bandwidth Product	I_C= -0.5A; V_{CE}= -10V		3		MHz

◆ **h_{FE-1} Classifications**

A	B	C
40-80	70-140	120-240